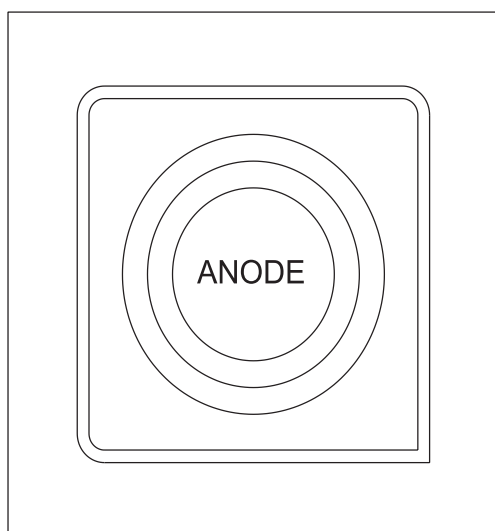


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	9.0 x 9.0 MILS
Die Thickness	7.9 MILS
Anode Bonding Pad Area	4.8 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



BACKSIDE CATHODE

R0

**GROSS DIE PER 4 INCH WAFER**

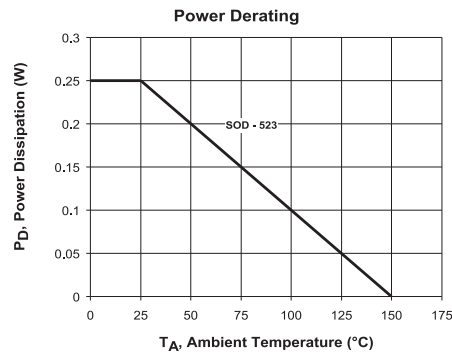
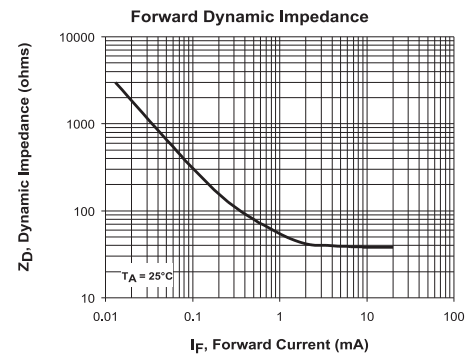
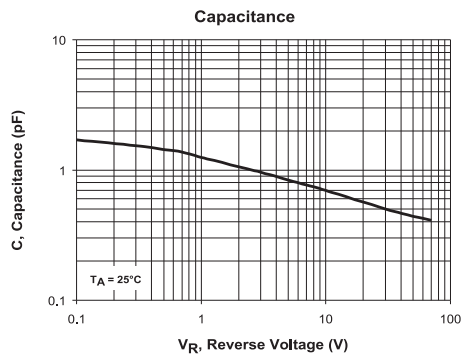
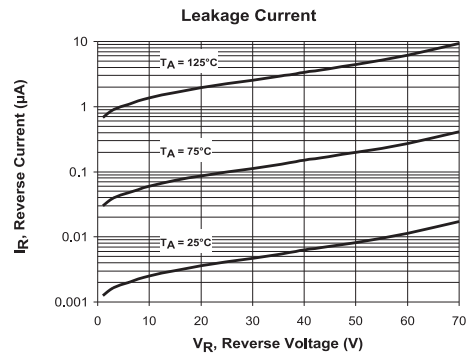
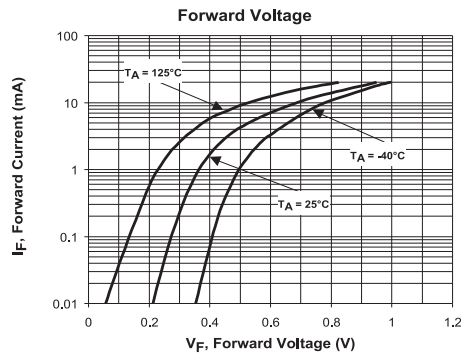
139,050

**PRINCIPAL DEVICE TYPES**

CMDD6263  
CMKD6263  
CMOD6263  
CMPD6263 SERIES  
CMSD6263 SERIES  
1N6263

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